

Satoshi Kurai

List of Publications by Year in descending order

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51
papers

840
citations

759233

12
h-index

477307

29
g-index

51
all docs

51
docs citations

51
times ranked

867
citing authors

#	ARTICLE	IF	CITATIONS
1	Direct Evidence that Dislocations are Non-Radiative Recombination Centers in GaN. Japanese Journal of Applied Physics, 1998, 37, L398-L400.	1.5	417
2	Photopumped Stimulated Emission from Homoepitaxial GaN Grown on Bulk GaN Prepared by Sublimation Method. Japanese Journal of Applied Physics, 1996, 35, L77-L79.	1.5	69
3	Superior Illuminant Characteristics of Color Rendering and Luminous Efficacy in Multilayered Phosphor Conversion White Light Sources Excited by Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2009, 48, 112101.	1.5	41
4	Nucleation Control in the Growth of Bulk GaN by Sublimation Method. Japanese Journal of Applied Physics, 1997, 36, L184-L186.	1.5	29
5	Growth and Characterization of Thick GaN by Sublimation Method and Homoepitaxial Growth by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, 1637-1640.	1.5	26
6	Inhomogeneous distribution of defect-related emission in Si-doped AlGaIn epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
7	Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method. Japanese Journal of Applied Physics, 2000, 39, 2394-2398.	1.5	16
8	Near-ultraviolet LED of the External Quantum Efficiency Over 45% and its Application to High-color Rendering Phosphor Conversion White LEDs. Journal of Light and Visual Environment, 2008, 32, 39-42.	0.2	15
9	Time-resolved spectroscopy of excitonic luminescence from GaN homoepitaxial layers. Journal of Applied Physics, 1999, 86, 7186-7188.	2.5	13
10	Separation of effects of InGaIn/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	1.5	13
11	Potential Barrier Formed Around Dislocations in InGaIn Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	1.5	13
12	Growth of GaN by Sublimation Technique and Homoepitaxial Growth by MOCVD. Materials Research Society Symposia Proceedings, 1996, 449, 15.	0.1	12
13	Surface Pretreatment of Bulk GaN for Homoepitaxial Growth by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 626-631.	1.5	11
14	Excitonic Emissions under High Excitation of Hexagonal GaN Single Crystal Grown by Sublimation Method. Japanese Journal of Applied Physics, 1999, 38, L102-L104.	1.5	11
15	Development of White Light Emitting Diodes by Multi-layered Red, Green, and Blue Phosphors Excited by Near-ultraviolet Light Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 43-45.	0.2	11
16	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaIn-based multiple quantum wells using rate equations of exciton recombination. Japanese Journal of Applied Physics, 2019, 58, SCCB02.	1.5	11
17	Growth and optical properties of AlN homoepitaxial layers grown by ammonia-source molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 461-464.	1.5	9
18	Growth and Luminescence Properties of Subsequently Grown AlInN Layers on AlN Homoepitaxial Layers by Ammonia Gas Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 3394-3396.	1.5	8

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19	Correlation between in-plane strain and optical polarization of Si-doped AlGa _x N epitaxial layers as a function of Al content and Si concentration. <i>Journal of Applied Physics</i> , 2012, 112, 033512.	2.5	8
20	Fabrication and Illuminance Properties of Phosphor-conversion Green Light-emitting Diode with a Luminous Efficacy over 100 lm/W. <i>Journal of Light and Visual Environment</i> , 2007, 31, 146-148.	0.2	8
21	Nanoscope spectroscopy of potential barriers formed around V-pits in InGa _x N/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	7
22	A novel colonoscope with high color-rendering white light-emitting diodes. <i>Gastrointestinal Endoscopy</i> , 2011, 73, 598-602.	1.0	6
23	Recombination dynamics of localized excitons in Al _x Ga _{1-x} N (0.37 x <math>< 0.81</math>) ternary alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2133-2135.	0.8	6
24	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGa _x N Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JL07.	1.5	6
25	Si concentration dependence of structural inhomogeneities in Si-doped Al _x Ga _{1-x} N/Al _y Ga _{1-y} N multiple quantum well structures ($x = 0.6$) and its relationship with internal quantum efficiency. <i>Journal of Applied Physics</i> , 2014, 116, .		5
26	Microscopic potential fluctuations in Si-doped AlGa _x N epitaxial layers with various AlN molar fractions and Si concentrations. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	5
27	Homoepitaxial growth of GaN thin layer by molecular beam epitaxy with an RF nitrogen plasma. <i>Vacuum</i> , 2000, 59, 277-283.	3.5	4
28	Image quality of a novel light-emitting diode (LED)-illuminated colonoscope. <i>Endoscopy</i> , 2016, 48, 934-938.	1.8	4
29	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al _{0.61} Ga _{0.39} N Epitaxial Layer. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700374.	1.5	4
30	Transmission Electron Microscopy of Sublimation-Grown GaN Single Crystal and GaN Homoepitaxial Film. <i>Japanese Journal of Applied Physics</i> , 1996, 35, L1318-L1320.	1.5	3
31	Effect of Cooling Process after GaN Epitaxial Growth by Radio-Frequency Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L1297-L1300.	1.5	3
32	Study on the Luminous and Thermal Characteristics of High-Power Near-Ultraviolet LED Packages with Various Chip Arrangements. <i>Journal of Light and Visual Environment</i> , 2009, 33, 142-146.	0.2	3
33	In vitrobactericidal effects of near-ultraviolet light from light-emitting diodes on <i>Helicobacter pylori</i> . <i>Scandinavian Journal of Gastroenterology</i> , 2013, 48, 1484-1486.	1.5	3
34	Spatially Resolved Spectroscopy of Blue and Green InGa _x N Quantum Wells by Scanning Near-Field Optical Microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700322.	1.5	3
35	Growth of homoepitaxial GaN layers and GaN/AlGa _x N multiple quantum wells on GaN single-crystal substrates by molecular-beam epitaxy. , 2002, 4776, 97.		2
36	Pre-treatment of GaN template for homoepitaxial growth by radio-frequency molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2002, 236, 66-70.	1.5	2

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37	Homoepitaxial Growth of GaN Layers by Reactive Molecular-Beam Epitaxy on Bulk GaN Single Crystals Prepared by Pressure-Controlled Solution Growth. Japanese Journal of Applied Physics, 2004, 43, 7454-7457.	1.5	2
38	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaIn/AlGaIn multiple quantum wells. Japanese Journal of Applied Physics, 2018, 57, 060311.	1.5	2
39	Dependence of Light Extraction From Near-Ultraviolet Light-Emitting Diodes on Refraction Index, Transmittance and Shape. Journal of Light and Visual Environment, 2009, 33, 137-141.	0.2	2
40	Development of Light Sources by Large-Scale Integrated Light-Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 238-240.	0.2	2
41	Correlation between dislocations and luminescence in GaN. , 1998, , .		1
42	Optical Properties of ZnCdS:I Orange and ZnSTe:I White Thin Film Phosphor for High Ra White LED. Journal of Light and Visual Environment, 2007, 31, 61-64.	0.2	1
43	Analysis of Chip/Bump/Ceramic Interface of Flip-Chip Bonded LED Directly on Ceramic Packages. Journal of Light and Visual Environment, 2008, 32, 234-237.	0.2	1
44	Evaluation on Reliability of White LED Light Source Directly Flip-Chip Bonded on Ceramic Substrates. Journal of Japan Institute of Electronics Packaging, 2009, 12, 72-78.	0.1	1
45	Stress distribution and dislocation dynamics in GaAs grown on Si by metalorganic chemical vapor deposition. Journal of Crystal Growth, 1994, 145, 321-325.	1.5	0
46	Defect identification in homoepitaxial- and ELO-grown GaN layers using bound-exciton Zeeman spectroscopies. Journal of Crystal Growth, 2000, 210, 216-219.	1.5	0
47	Effect of pre-treatment of GaN substrate for homoepitaxial growth by rf MBE. , 2000, , .		0
48	Effect of Package Density on Luminous Efficiency of Direct Flip-Chip Bonded LED for the Phosphor Conversion Lighting. Journal of Japan Institute of Electronics Packaging, 2010, 13, 58-62.	0.1	0
49	A novel imaging system of optical detection on cancers and tissues in gastrointestinal endoscope using high-color-rendering white and color tunable LEDs. Proceedings of SPIE, 2010, , .	0.8	0
50	Temperature-dependent cathodoluminescence mapping of InGaIn epitaxial layers with different In compositions. Japanese Journal of Applied Physics, 2019, 58, SCCB13.	1.5	0
51	Study on higher-energy emission observed locally around V-pits on InGaIn/GaN quantum wells grown on moderate-temperature GaN. Journal of Applied Physics, 2021, 130, 053103.	2.5	0